

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Q _g Typ	I _D Max T _C = +25°C (Note 10)
40V	3mΩ @ V _{GS} = 10V	83nC	100A
	5mΩ @ V _{GS} = 4.5V	35nC	100A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – Minimizes Power Losses
- Low Q_g – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

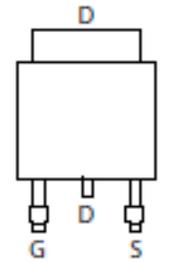
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters
- Motor Control

Mechanical Data

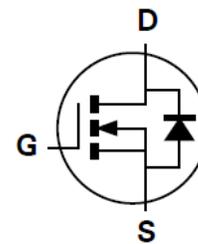
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top view



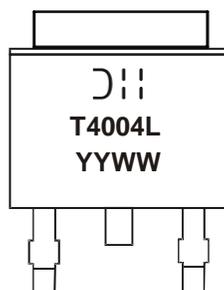
Equivalent Circuit

Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH4004LK3Q-13	TO252	2,500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



⌋|| = Manufacturer's Marking
 T4004L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Digit of Year (ex: 16 = 2016)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	40	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	I _D	T _C = +25°C (Note 10)	100
		T _C = +100°C	100
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	200	A
Maximum Continuous Body Diode Forward Current (Note 7)	I _S	100	A
Avalanche Current, L = 0.2mH	I _{AS}	30	A
Avalanche Energy, L = 0.2mH	E _{AS}	90	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6) T _A = +25°C	P _D	3.9	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	38	°C/W
Total Power Dissipation (Note 7) T _C = +25°C	P _D	180	W
Thermal Resistance, Junction to Case (Note 7)	R _{θJC}	0.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current, T _J = +25°C	I _{DSS}	—	—	1	µA	V _{DS} = 32V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	2.4	3	mΩ	V _{GS} = 10V, I _D = 50A
		—	4	5	mΩ	V _{GS} = 4.5V, I _D = 50A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 50A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iSS}	—	4,450	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	1,407	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	74	—	pF	
Gate Resistance	R _g	—	0.7	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	35	—	nC	V _{DS} = 20V, I _D = 30A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	83	—	nC	
Gate-Source Charge	Q _{gs}	—	10	—	nC	
Gate-Drain Charge	Q _{gd}	—	11.2	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.9	—	ns	V _{GS} = 10V, V _{DS} = 20V, R _G = 1.6Ω, I _D = 30A
Turn-On Rise Time	t _r	—	13.2	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	25.8	—	ns	
Turn-Off Fall Time	t _f	—	7.9	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	48	—	ns	I _F = 50A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	72	—	nC	I _F = 50A, di/dt = 100A/µs

- Notes:
- Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions while operating in a steady state.
 - Thermal resistance from junction to solder point (on the exposed drain pin).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.
 - Package Limited.

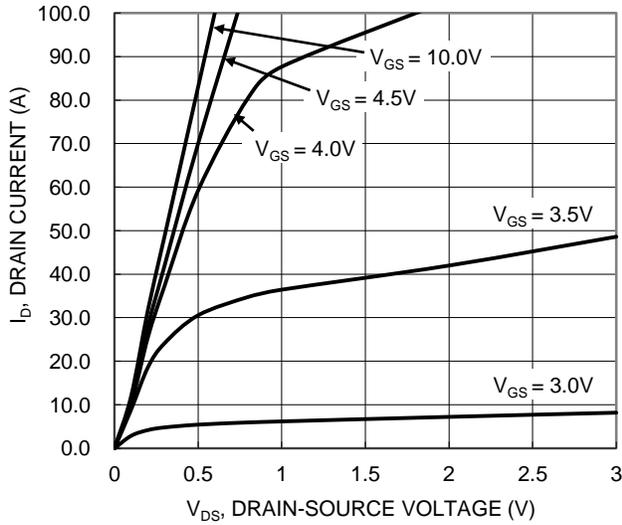


Figure 1. Typical Output Characteristic

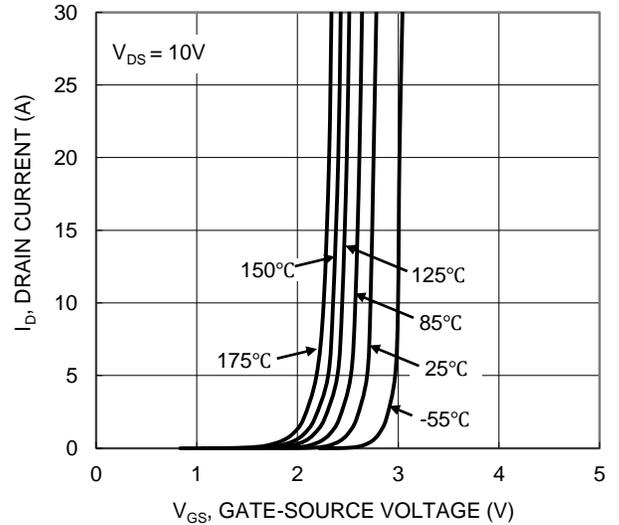


Figure 2. Typical Transfer Characteristic

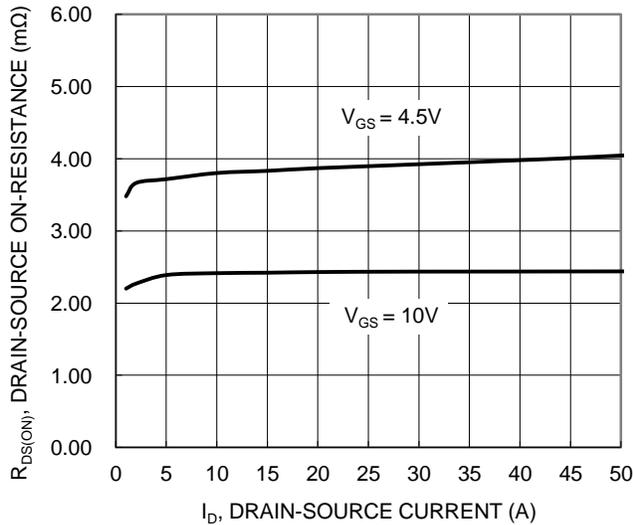


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

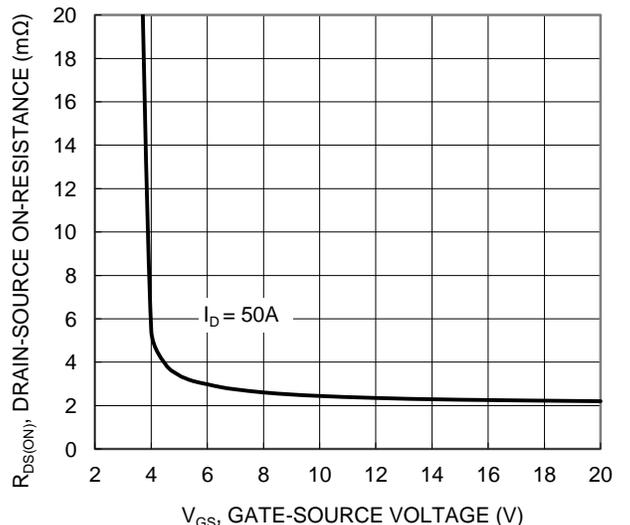


Figure 4. Typical Transfer Characteristic

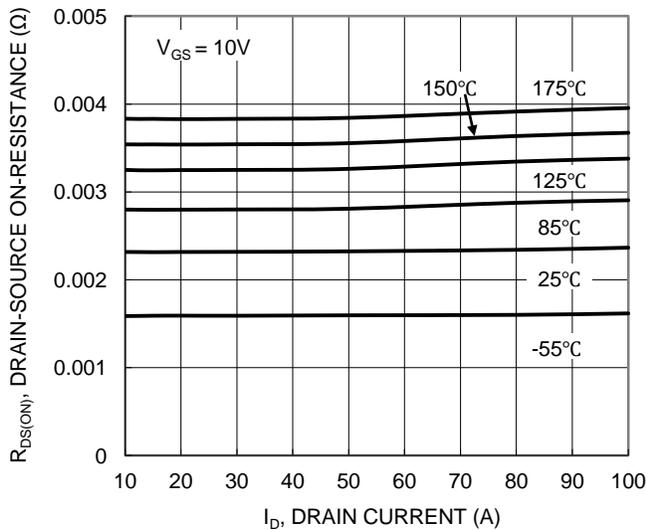


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

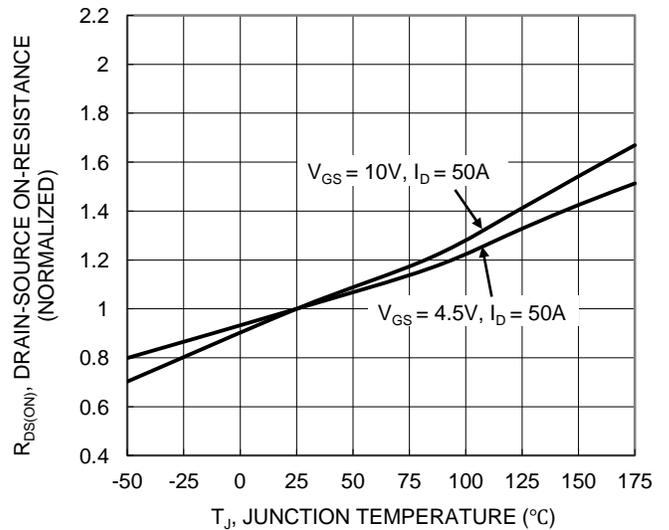


Figure 6. On-Resistance Variation with Temperature

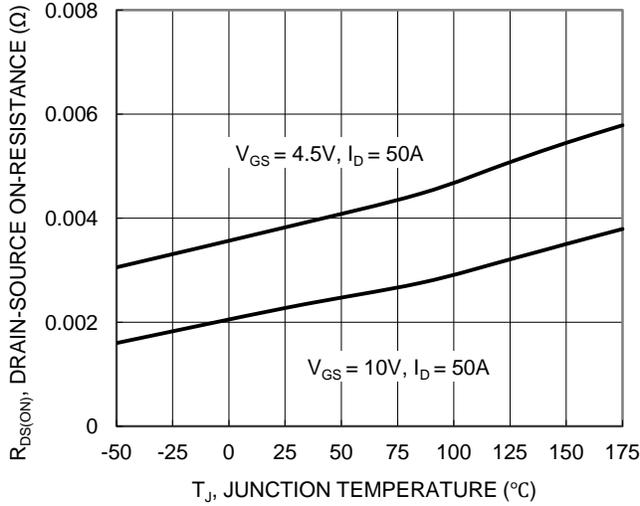


Figure 7. On-Resistance Variation with Temperature

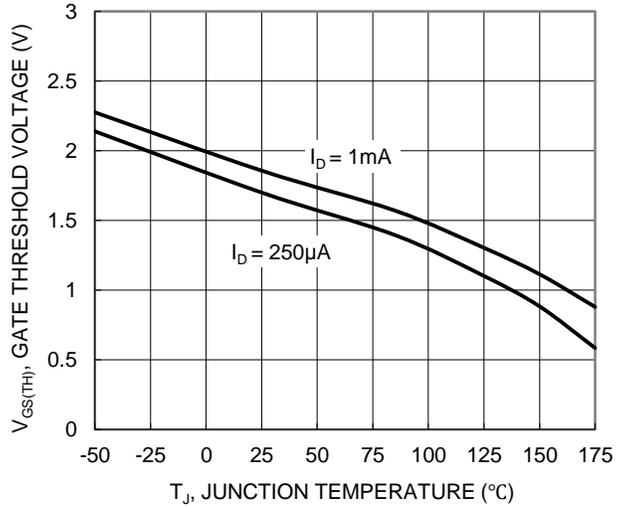


Figure 8. Gate Threshold Variation vs. Temperature

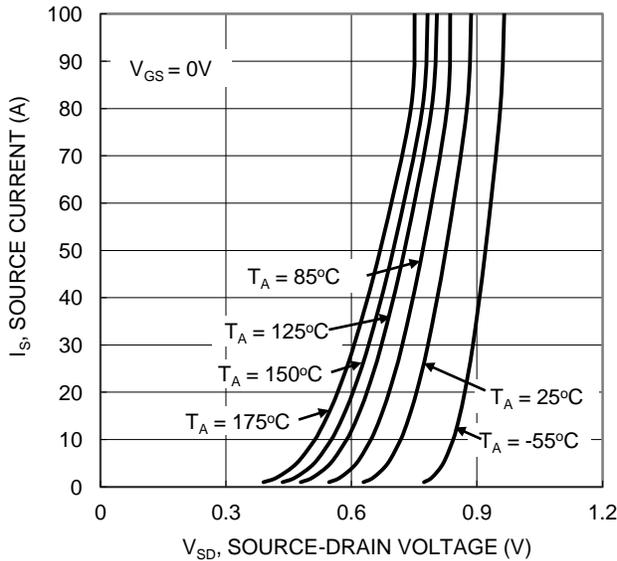


Figure 9. Diode Forward Voltage vs. Current

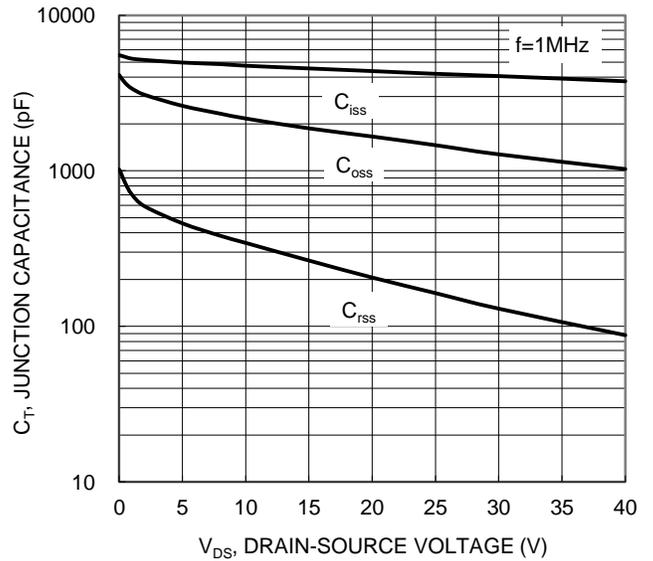


Figure 10. Typical Junction Capacitance

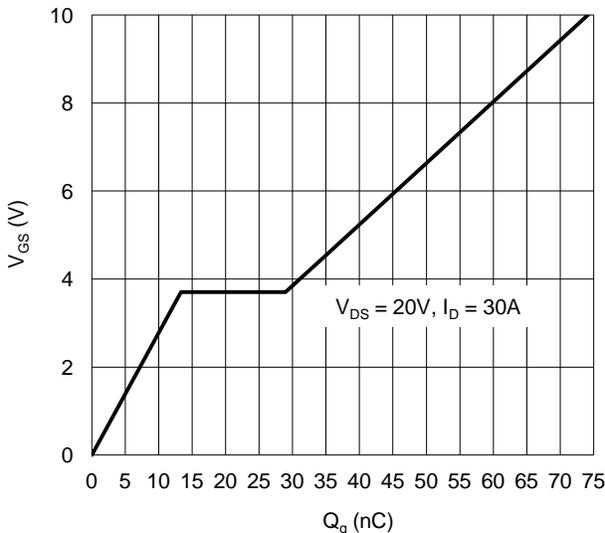


Figure 11. Gate Charge

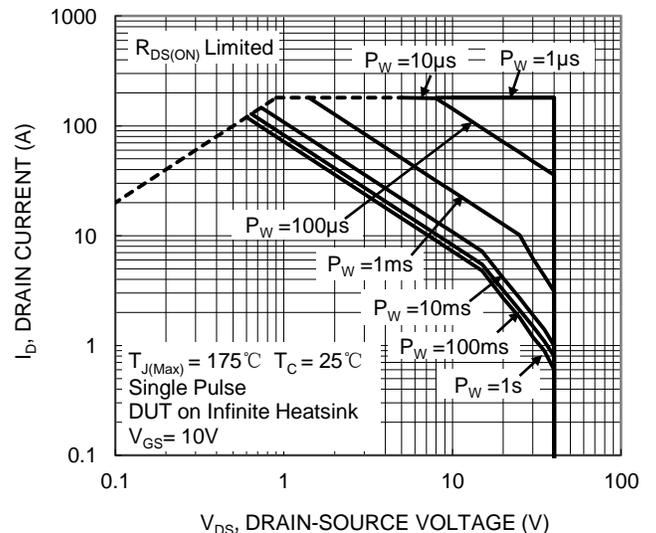


Figure 12. SOA, Safe Operation Area

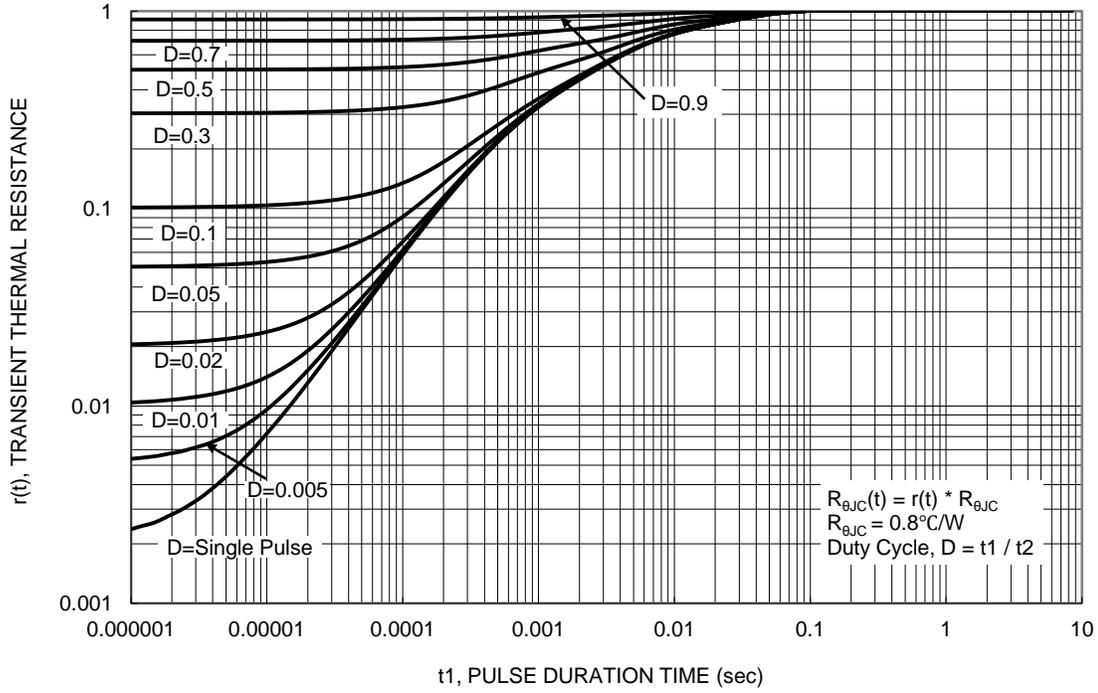
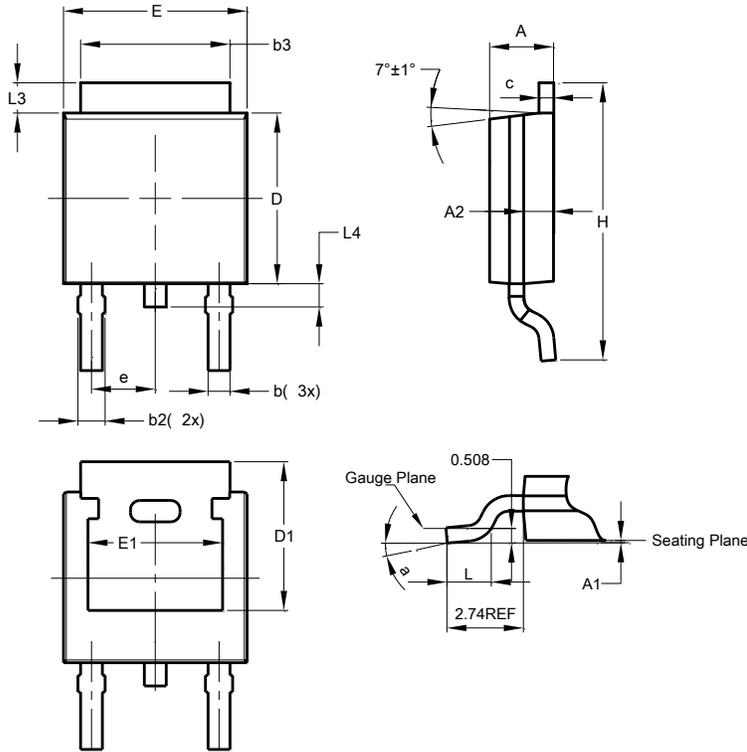


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)

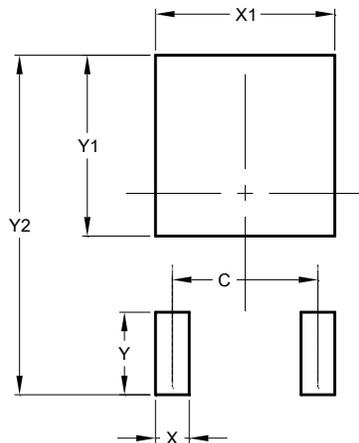


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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